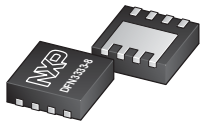




**THE DATASHEET OF  
PSMN3R8-30LL,115**





# PSMN3R8-30LL

N-channel DFN3333-8 30 V 3.7 mΩ logic level MOSFET

Rev. 4 — 12 December 2011

Product data sheet

## 1. Product profile

### 1.1 General description

Logic level N-channel MOSFET in DFN3333-8 package qualified to 150 °C. This product is designed and qualified for use in a wide range of industrial, communications and power supply equipment.

### 1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for logic level gate drive sources
- Small footprint for compact designs

### 1.3 Applications

- Battery protection
- DC-to-DC converters
- Load switching
- Power ORing

### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \geq 25\text{ °C}; T_j \leq 150\text{ °C}$	-	-	30	V
$I_D$	drain current	$T_{mb} = 25\text{ °C}; V_{GS} = 10\text{ V};$ see <a href="#">Figure 2</a>	-	-	40	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C};$ see <a href="#">Figure 1</a>	-	-	69	W
$T_j$	junction temperature		-55	-	150	°C
<b>Static characteristics</b>						
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 4.5\text{ V}; I_D = 10\text{ A}; T_j = 25\text{ °C}$	-	4.5	5.8	mΩ
		$V_{GS} = 10\text{ V}; I_D = 10\text{ A}; T_j = 100\text{ °C};$ see <a href="#">Figure 12</a>	-	-	5.1	mΩ
		$V_{GS} = 10\text{ V}; I_D = 10\text{ A}; T_j = 25\text{ °C};$ see <a href="#">Figure 13</a>	-	3	3.7	mΩ

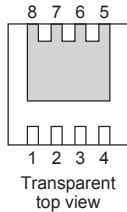
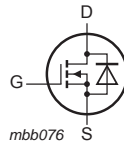


**Table 1. Quick reference data ...continued**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Dynamic characteristics</b>						
$Q_{GD}$	gate-drain charge	$V_{GS} = 10\text{ V}; I_D = 15\text{ A}; V_{DS} = 15\text{ V};$ see <a href="#">Figure 14</a> ; see <a href="#">Figure 15</a>	-	5.3	-	nC
$Q_{G(tot)}$	total gate charge	$V_{GS} = 4.5\text{ V}; I_D = 15\text{ A}; V_{DS} = 15\text{ V};$ see <a href="#">Figure 14</a> ; see <a href="#">Figure 15</a>	-	38	-	nC
<b>Avalanche ruggedness</b>						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10\text{ V}; T_{j(\text{init})} = 25\text{ }^\circ\text{C}; I_D = 40\text{ A};$ $V_{sup} \leq 30\text{ V}; \text{unclamped}; R_{GS} = 50\text{ }\Omega$	-	-	109	mJ

## 2. Pinning information

**Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	 <p>Transparent top view</p>	 <p>mbb076</p>
2	S	source		
3	S	source		
4	G	gate		
5,6,7,8	D	drain		
mb	D	mounting base; connected to drain		

**SOT873-1 (DFN3333-8)**

## 3. Ordering information

**Table 3. Ordering information**

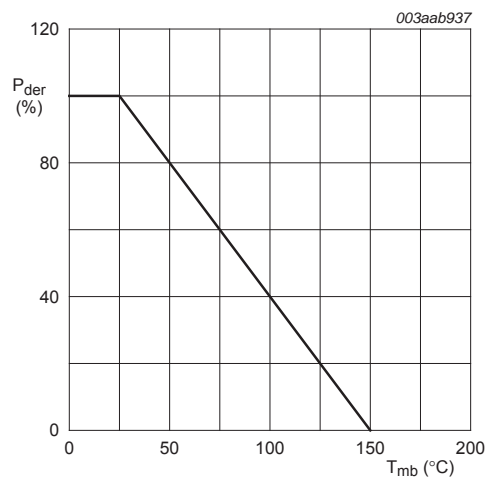
Type number	Package		Version
	Name	Description	
PSMN3R8-30LL	DFN3333-8	plastic thermal enhanced very thin small outline package; no leads; 8 terminals	SOT873-1

## 4. Limiting values

**Table 4. Limiting values**

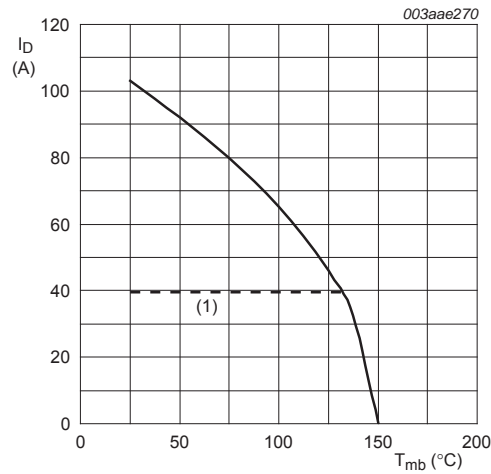
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \geq 25\text{ °C}$ ; $T_j \leq 150\text{ °C}$	-	30	V
$V_{DGR}$	drain-gate voltage	$T_j \leq 150\text{ °C}$ ; $T_j \geq 25\text{ °C}$ ; $R_{GS} = 20\text{ k}\Omega$	-	30	V
$V_{GS}$	gate-source voltage		-20	20	V
$I_D$	drain current	$V_{GS} = 10\text{ V}$ ; $T_{mb} = 100\text{ °C}$ ; see <a href="#">Figure 2</a>	-	40	A
		$V_{GS} = 10\text{ V}$ ; $T_{mb} = 25\text{ °C}$ ; see <a href="#">Figure 2</a>	-	40	A
$I_{DM}$	peak drain current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; $T_{mb} = 25\text{ °C}$ ; see <a href="#">Figure 3</a>	-	413	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C}$ ; see <a href="#">Figure 1</a>	-	69	W
$T_{stg}$	storage temperature		-55	150	°C
$T_j$	junction temperature		-55	150	°C
$T_{sld(M)}$	peak soldering temperature		-	260	°C
<b>Source-drain diode</b>					
$I_S$	source current	$T_{mb} = 25\text{ °C}$	-	40	A
$I_{SM}$	peak source current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; $T_{mb} = 25\text{ °C}$	-	413	A
<b>Avalanche ruggedness</b>					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10\text{ V}$ ; $T_{j(\text{init})} = 25\text{ °C}$ ; $I_D = 40\text{ A}$ ; $V_{sup} \leq 30\text{ V}$ ; unclamped; $R_{GS} = 50\text{ }\Omega$	-	109	mJ



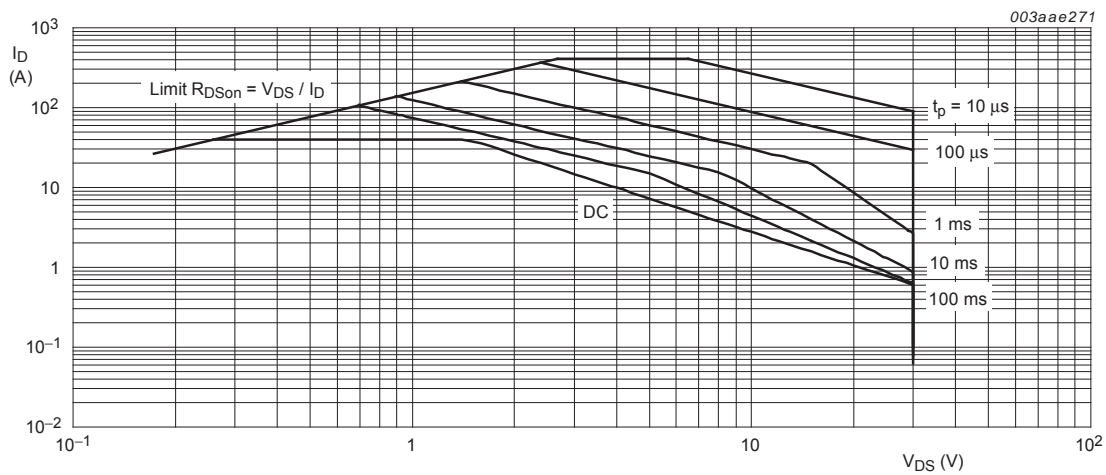
$$P_{der} = \frac{P_{tot}}{P_{tot(25\text{ °C})}} \times 100\%$$

**Fig 1. Normalized total power dissipation as a function of solder point temperature**



$V_{GS} \geq 10V$ ; (1) Capped at 40 A due to package.

**Fig 2. Continuous drain current as a function of mounting base temperature**



$T_{mb} = 25^\circ C$ ;  $I_{DM}$  is single pulse

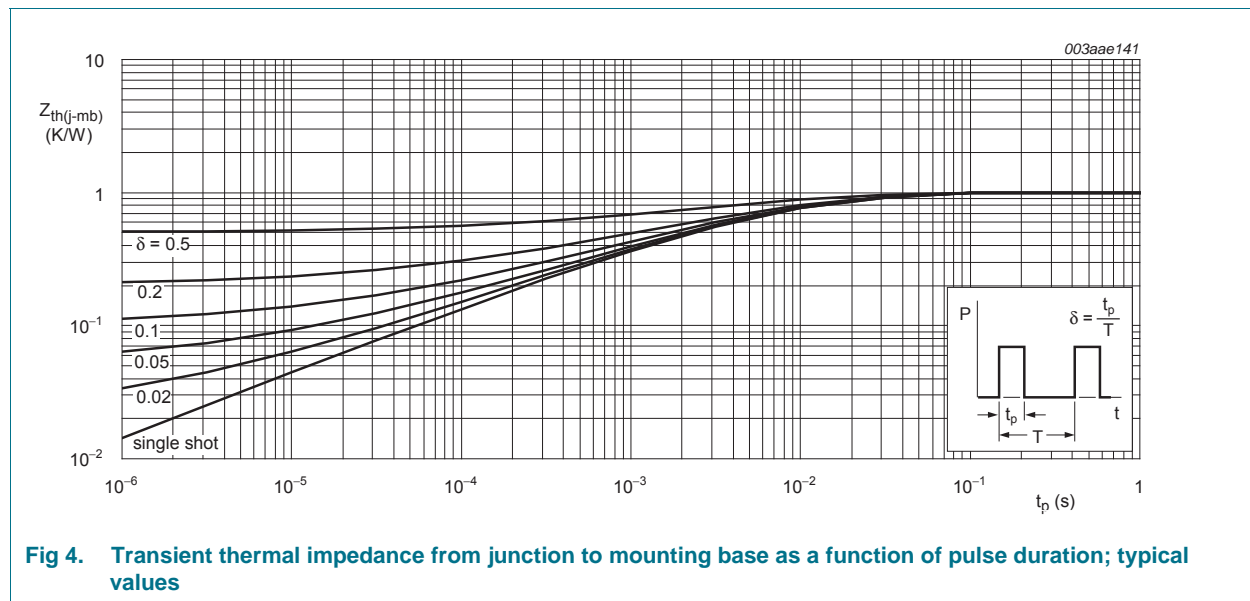
**Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage**

### 5. Thermal characteristics

**Table 5. Thermal characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see <a href="#">Figure 4</a>	-	1	1.3	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient		[1]	53	60	K/W

[1]  $R_{th(j-a)}$  is guaranteed by design and assumes that the device is mounted on a 40mm x 40mm x 70μm copper pad at 20°C ambient temperature. In practice  $R_{th(j-a)}$  will be determined by the customer's PCB characteristics



**Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration; typical values**

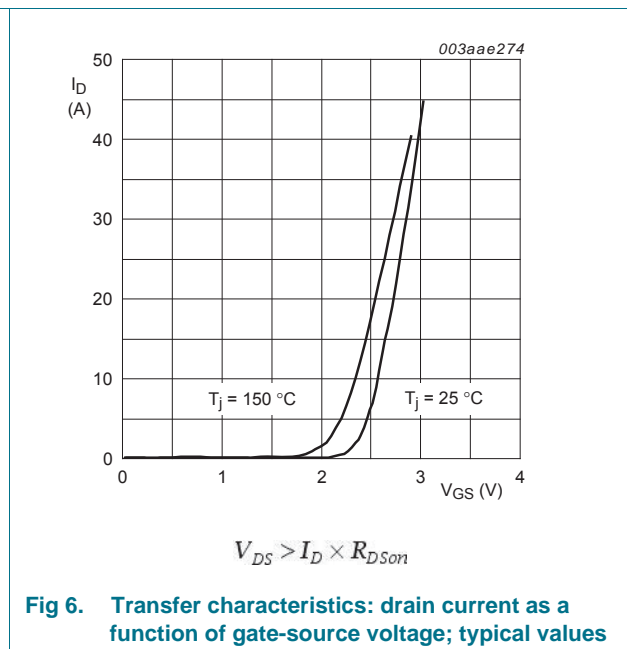
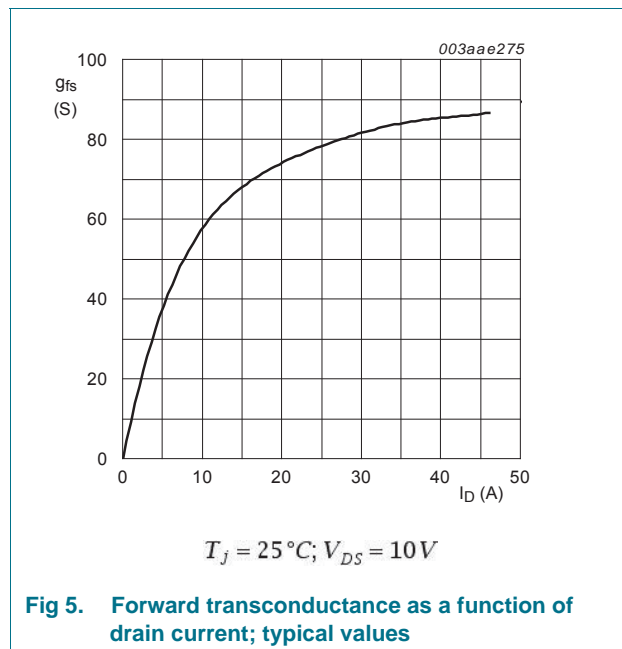
## 6. Characteristics

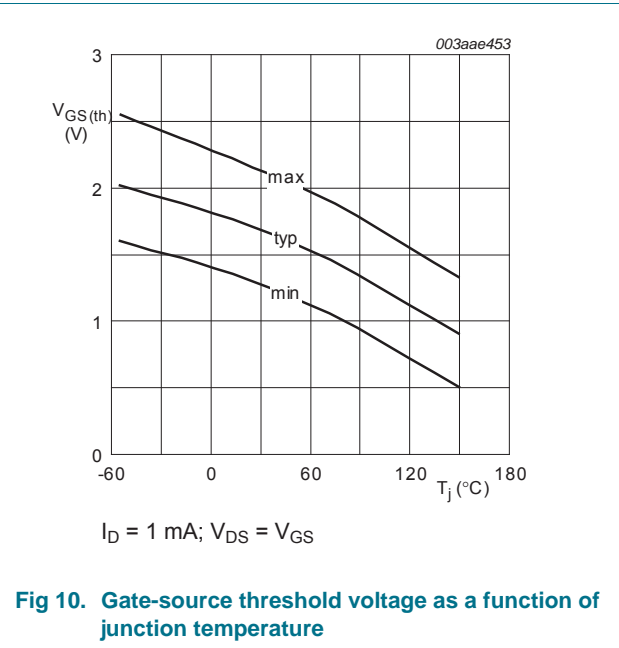
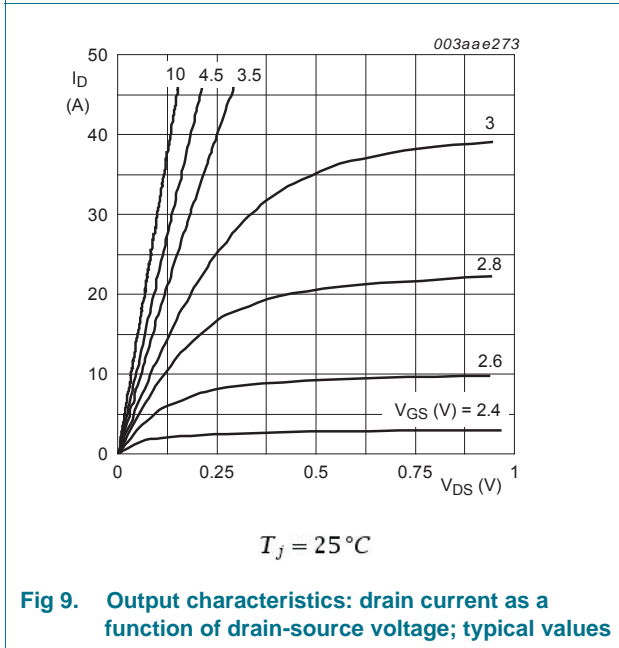
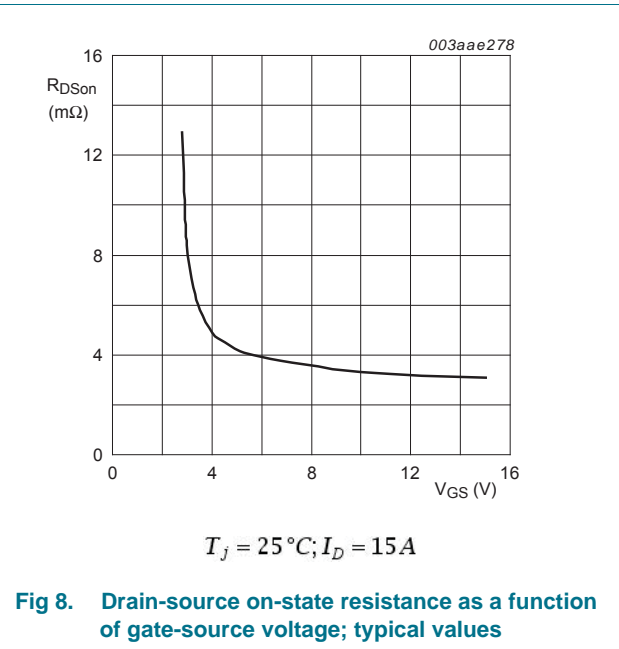
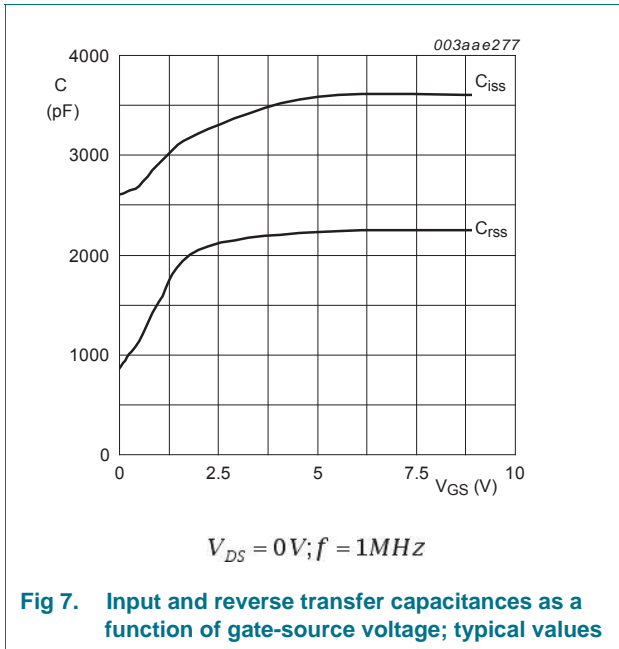
Table 6. Characteristics

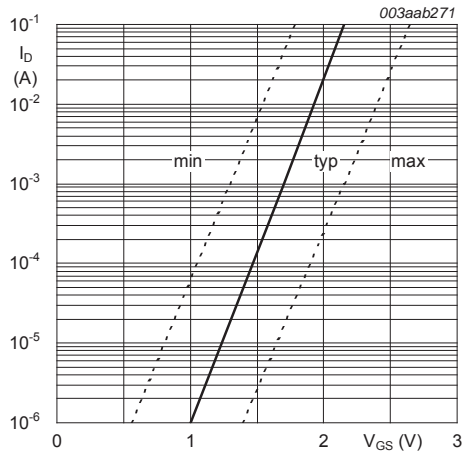
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ }^\circ\text{C}$	27	-	-	V
		$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	30	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 150 \text{ }^\circ\text{C};$ see <a href="#">Figure 10</a>	0.5	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ\text{C};$ see <a href="#">Figure 11</a> ; see <a href="#">Figure 10</a>	1.3	1.7	2.15	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ }^\circ\text{C};$ see <a href="#">Figure 10</a>	-	-	2.6	V
$I_{DSS}$	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	0.05	1	μA
		$V_{DS} = 30 \text{ V}; V_{GS} = 10 \text{ V}; T_j = 125 \text{ }^\circ\text{C}$	-	-	50	μA
$I_{GSS}$	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	5	100	nA
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	5	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 10 \text{ A}; T_j = 25 \text{ }^\circ\text{C}$	-	4.5	5.8	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 10 \text{ A}; T_j = 100 \text{ }^\circ\text{C};$ see <a href="#">Figure 12</a>	-	-	5.1	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 10 \text{ A}; T_j = 150 \text{ }^\circ\text{C};$ see <a href="#">Figure 12</a>	-	5.4	6.7	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 10 \text{ A}; T_j = 25 \text{ }^\circ\text{C};$ see <a href="#">Figure 13</a>	-	3	3.7	mΩ
$R_G$	internal gate resistance (AC)	$f = 1 \text{ MHz}$	-	1	-	Ω
<b>Dynamic characteristics</b>						
$Q_{G(tot)}$	total gate charge	$I_D = 15 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 10 \text{ V};$ see <a href="#">Figure 14</a> ; see <a href="#">Figure 15</a>	-	38	-	nC
		$I_D = 15 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$ see <a href="#">Figure 14</a> ; see <a href="#">Figure 15</a>	-	18	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	35	-	nC
$Q_{GS}$	gate-source charge	$I_D = 15 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 10 \text{ V};$ see <a href="#">Figure 14</a> ; see <a href="#">Figure 15</a>	-	6.5	-	nC
$Q_{GS(th)}$	pre-threshold gate-source charge	$I_D = 15 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 10 \text{ V};$ see <a href="#">Figure 14</a>	-	3.5	-	nC
$Q_{GS(th-pl)}$	post-threshold gate-source charge		-	3	-	nC
$Q_{GD}$	gate-drain charge	$I_D = 15 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 10 \text{ V};$ see <a href="#">Figure 14</a> ; see <a href="#">Figure 15</a>	-	5.3	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	$V_{DS} = 15 \text{ V};$ see <a href="#">Figure 14</a> ; see <a href="#">Figure 15</a>	-	2.8	-	V
$C_{iss}$	input capacitance	$V_{DS} = 15 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ }^\circ\text{C};$ see <a href="#">Figure 16</a>	-	2085	-	pF
$C_{oss}$	output capacitance		-	396	-	pF
$C_{rSS}$	reverse transfer capacitance		-	187	-	pF

Table 6. Characteristics ...continued

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$t_{d(on)}$	turn-on delay time	$V_{DS} = 15\text{ V}; R_L = 1\ \Omega; V_{GS} = 4.5\text{ V};$ $R_{G(ext)} = 4.7\ \Omega; T_j = 25\text{ }^\circ\text{C}$	-	27	-	ns
$t_r$	rise time		-	67	-	ns
$t_{d(off)}$	turn-off delay time		-	39	-	ns
$t_f$	fall time		-	18	-	ns
<b>Source-drain diode</b>						
$V_{SD}$	source-drain voltage	$I_S = 10\text{ A}; V_{GS} = 0\text{ V}; T_j = 25\text{ }^\circ\text{C};$ see <a href="#">Figure 17</a>	-	0.85	1.5	V
$t_{rr}$	reverse recovery time	$I_S = 15\text{ A}; di_S/dt = 100\text{ A}/\mu\text{s};$ $V_{GS} = 0\text{ V}; V_{DS} = 15\text{ V}$	-	36	-	ns
$Q_r$	recovered charge		-	30	-	nC

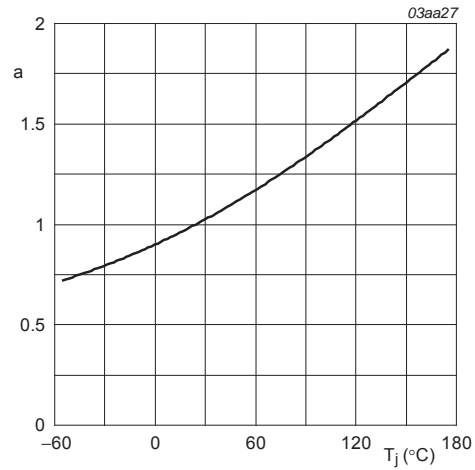






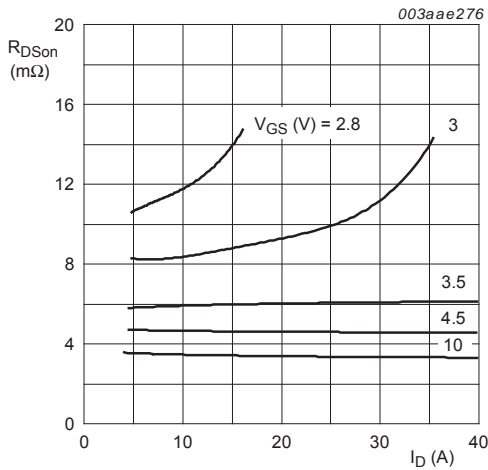
$T_j = 25^\circ\text{C}; V_{DS} = 5\text{V}$

**Fig 11. Sub-threshold drain current as a function of gate-source voltage**



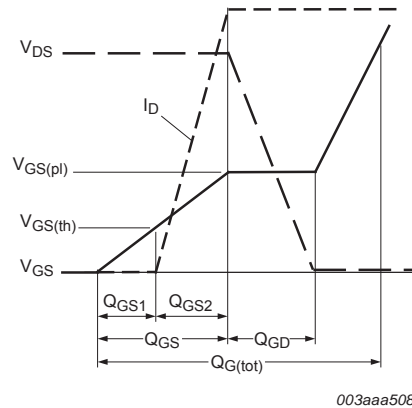
$$a = \frac{R_{DSon}}{R_{DSon}(25^\circ\text{C})}$$

**Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature**

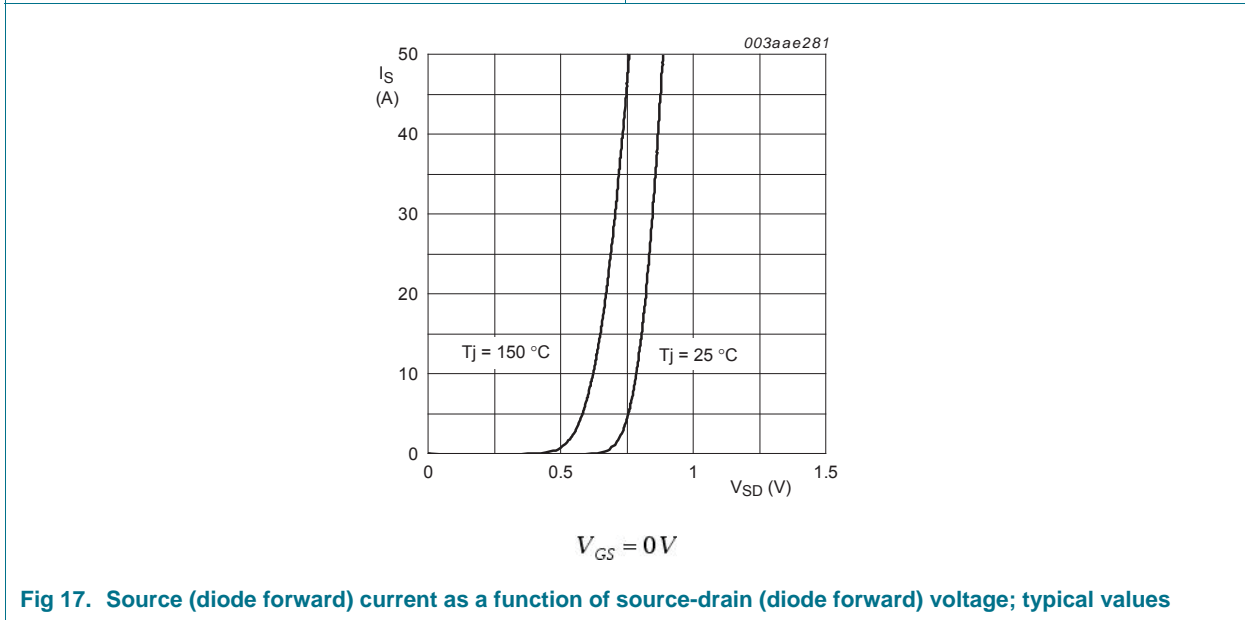
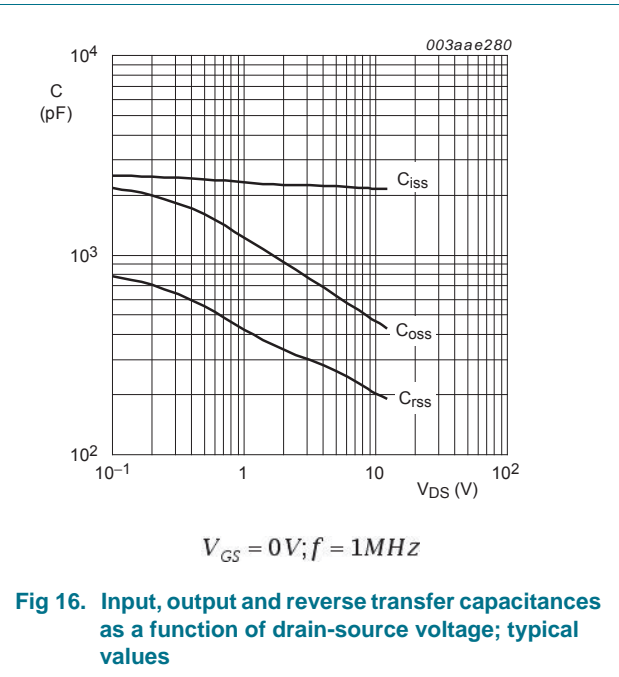
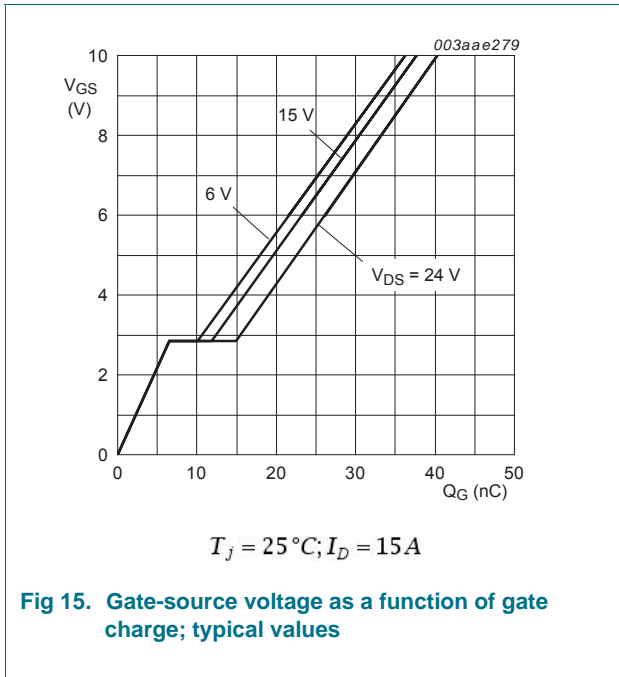


$T_j = 25^\circ\text{C}$

**Fig 13. Drain-source on-state resistance as a function of drain current; typical values**



**Fig 14. Gate charge waveform definitions**



## 7. Package outline

DFN3333-8: plastic thermal enhanced very thin small outline package; no leads;  
8 terminals; body 3.3 x 3.3 x 1.0 mm

SOT873-1

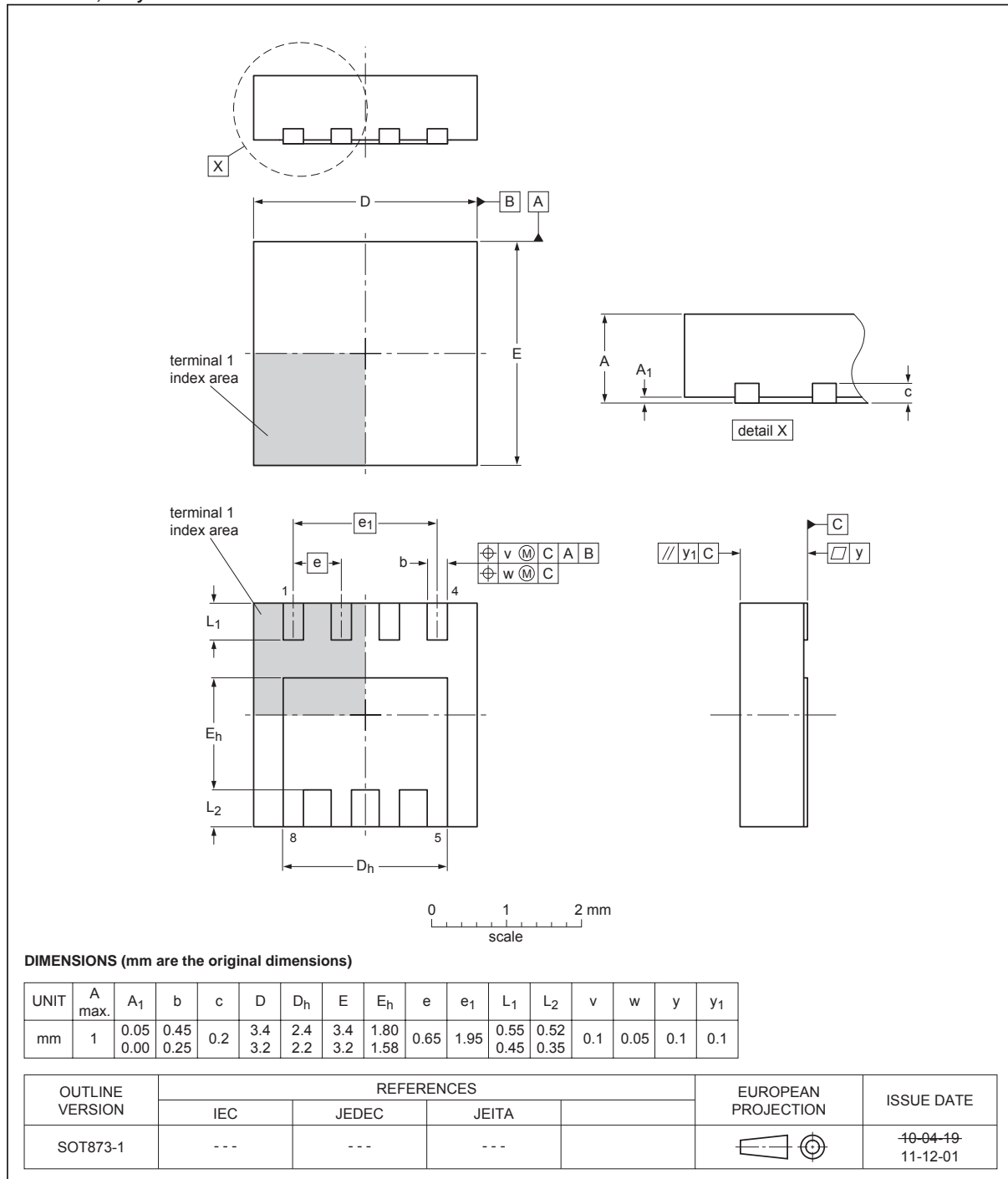


Fig 18. Package outline SOT873-1 (DFN3333-8)

## 8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN3R8-30LL v.4	20111212	Product data sheet	-	PSMN3R8-30LL v.3
Modifications:	• Various changes to content.			
PSMN3R8-30LL v.3	20100818	Product data sheet	-	PSMN3R8-30LL v.2

## 9. Legal information

### 9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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For more information, please visit: <http://www.nxp.com>

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